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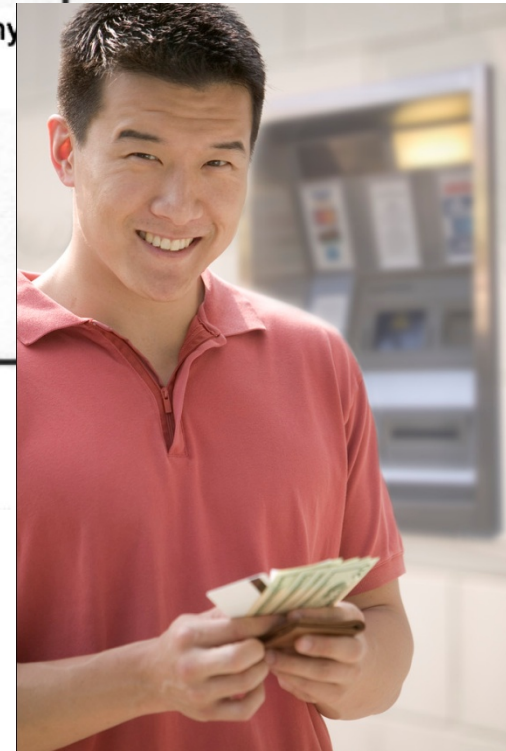
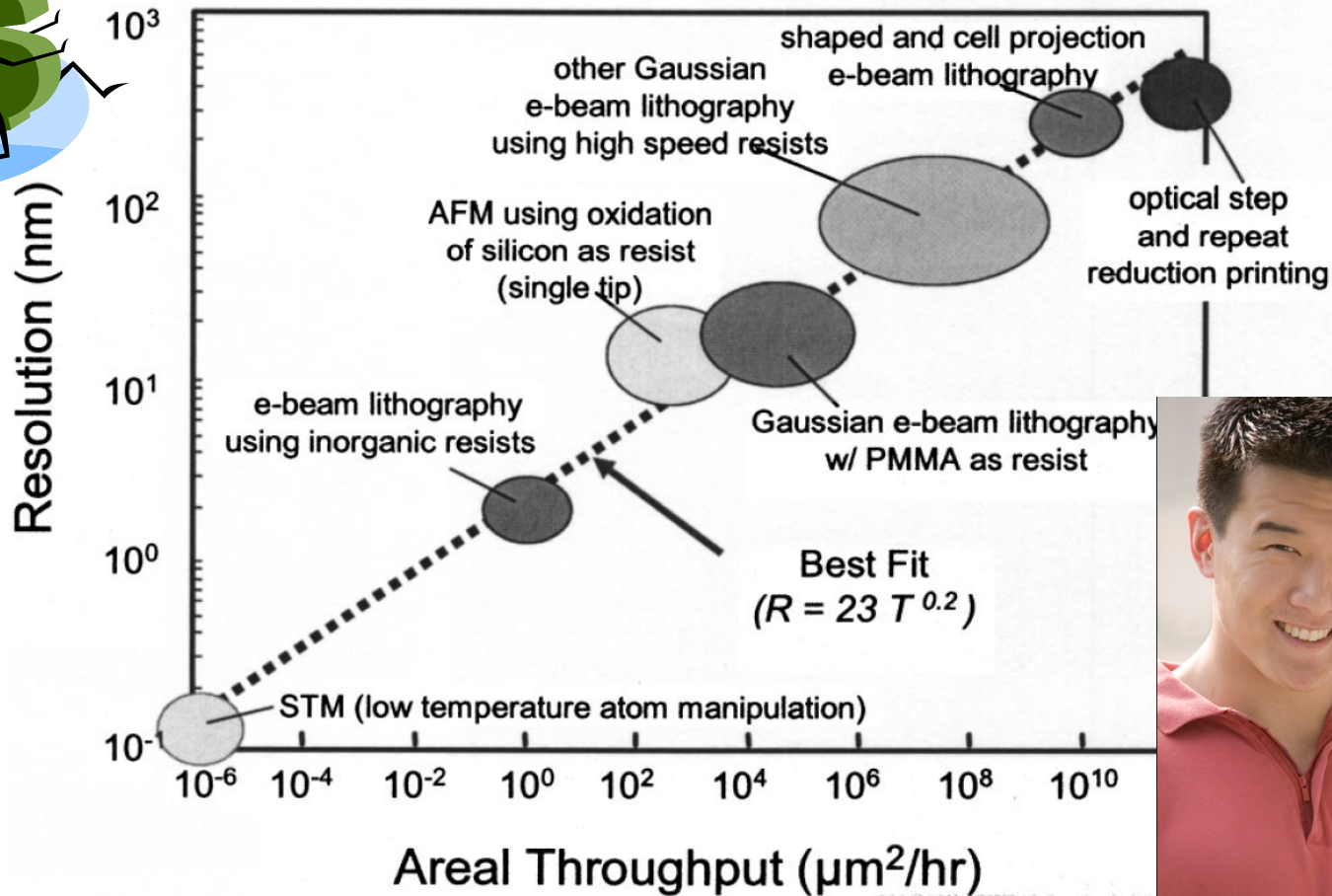
# **Nanometer Scale Patterning and Processing**

Spring 2016

## **Lecture 16**

### **Electron Optics and Lithography**

# Resolution and Throughput for Lithography



## Tennant's Law

Courtesy of Donald Tennant, Cornell Nanofabrication Facility

ECE 695 Nanometer Scale Patterning and Processing

# Electron-optics

$\lambda \sim 0.004 \text{ nm}$  ( $0.04 \text{ \AA}$ )  
at 100keV

$p = \lambda / \sin \alpha$  (only normal incidence)

$\alpha \sim 10^{-2}$  radians

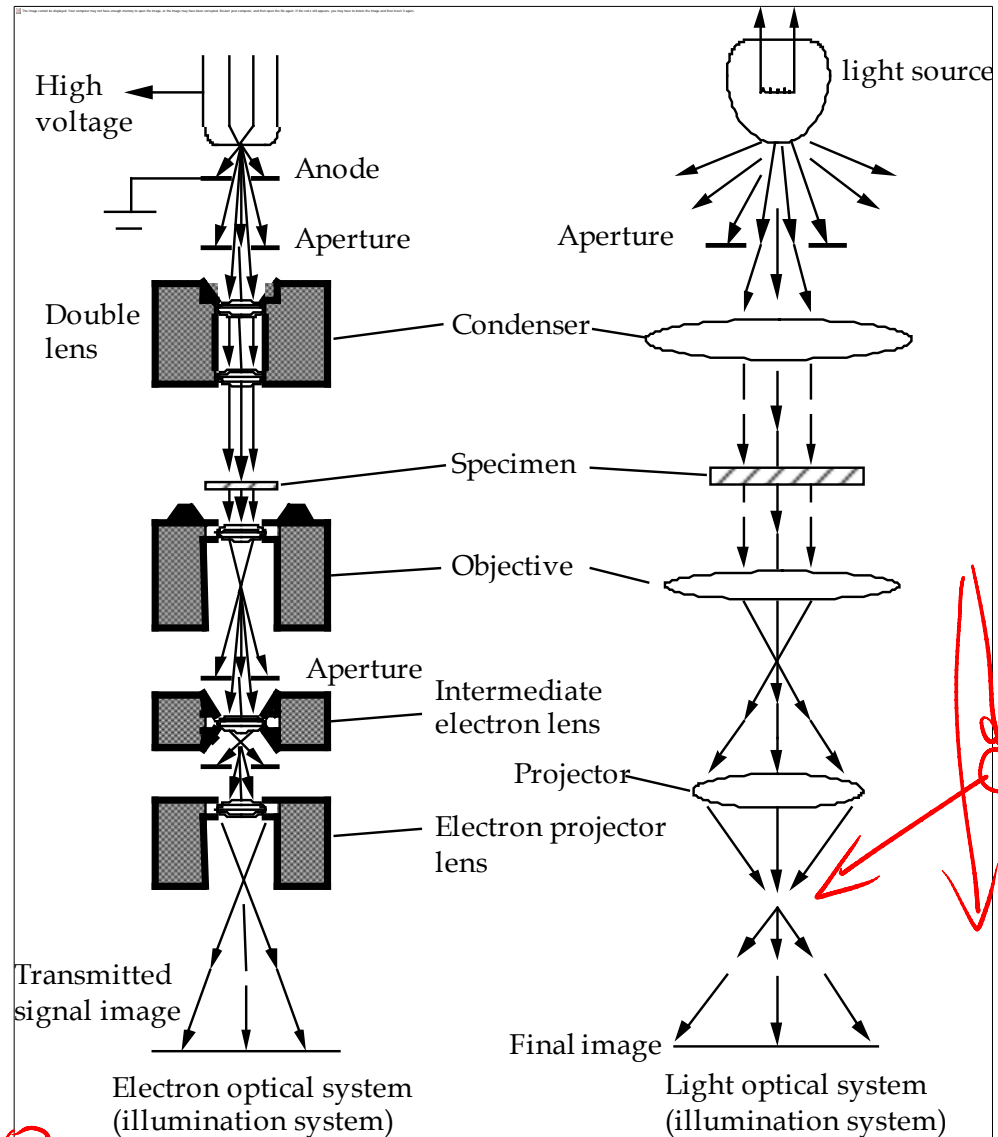
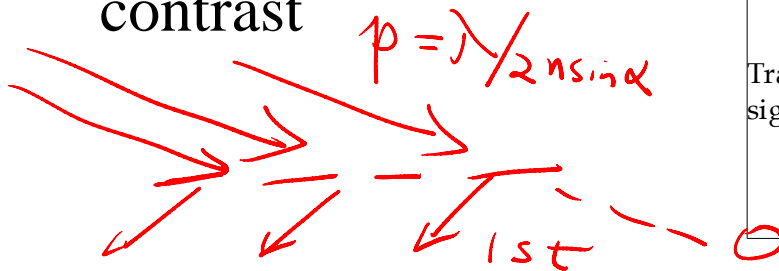
large angle scattering

are inelastic  $\rightarrow$

wavelength changed

$\rightarrow$  reduced image

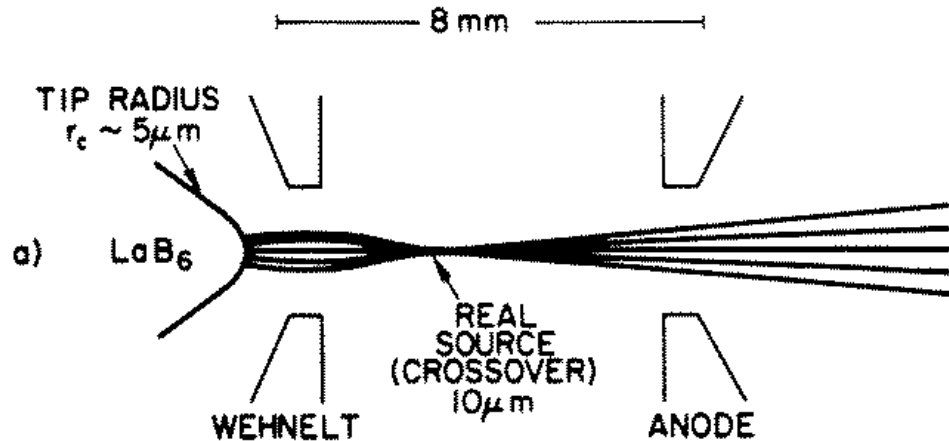
contrast



# Electron Source

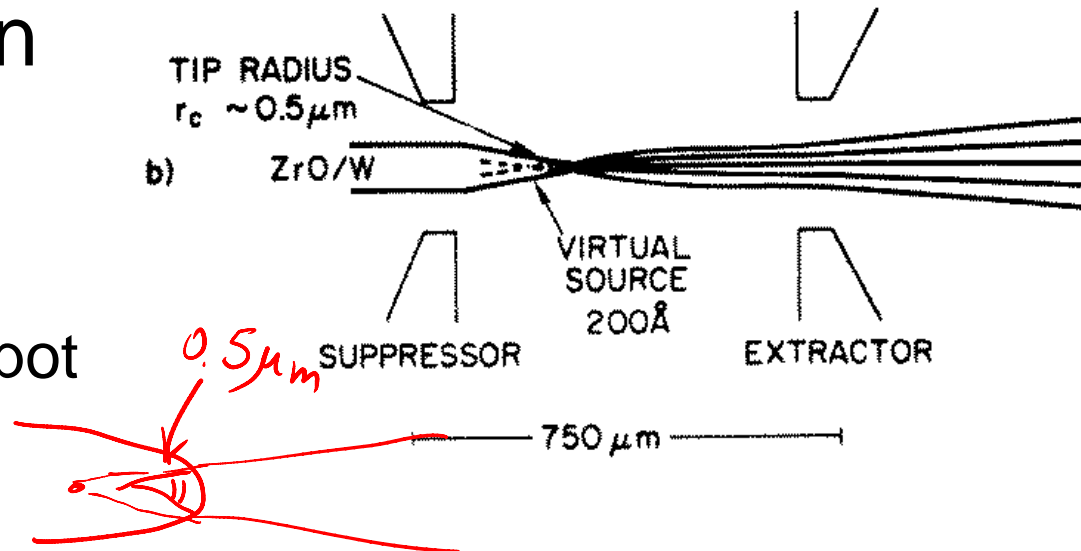
LaB<sub>6</sub>

higher total current  
larger beam spot

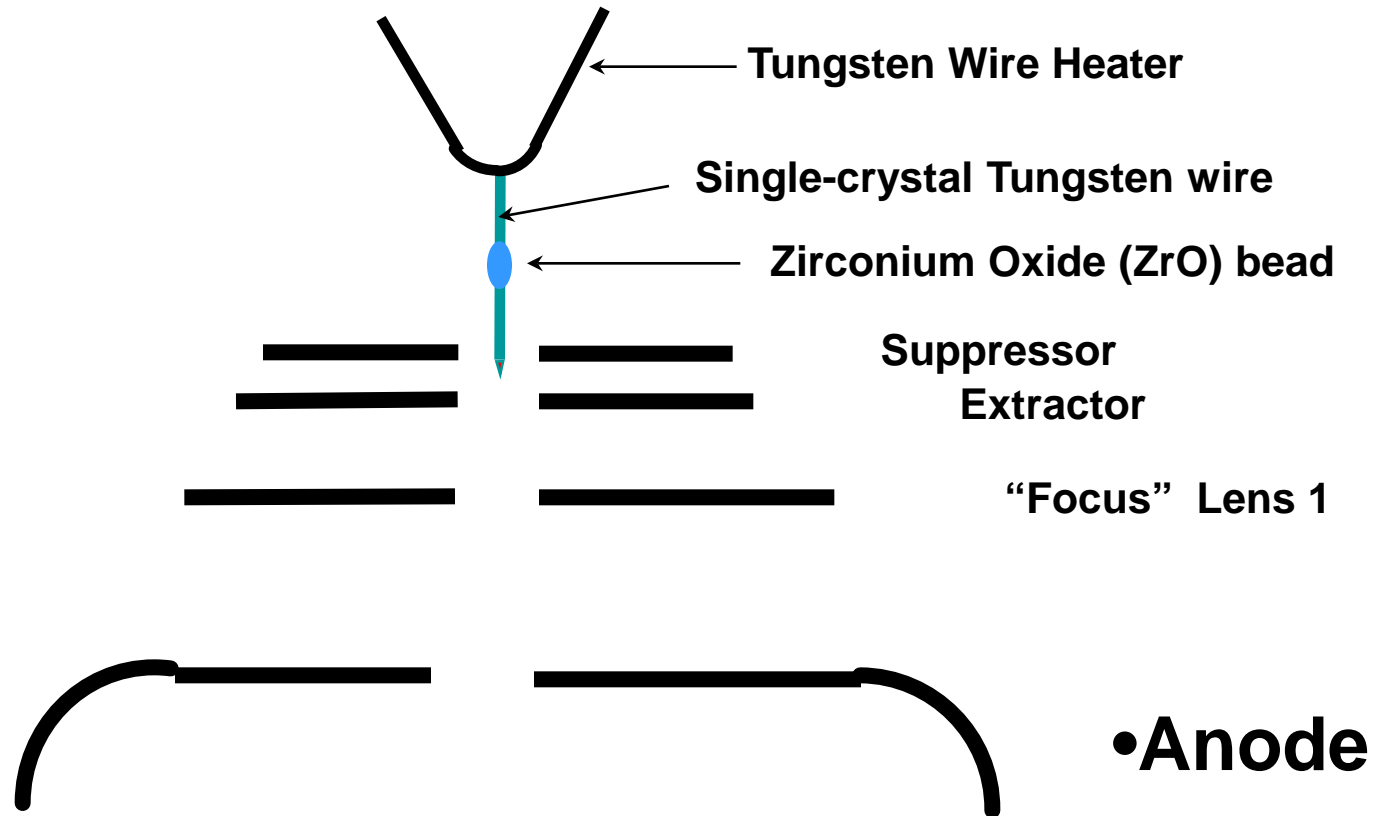


Field Emission

no crossover  
lower  $\Delta E$   
smaller beam spot



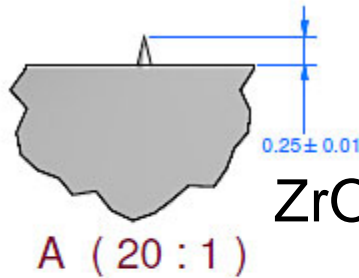
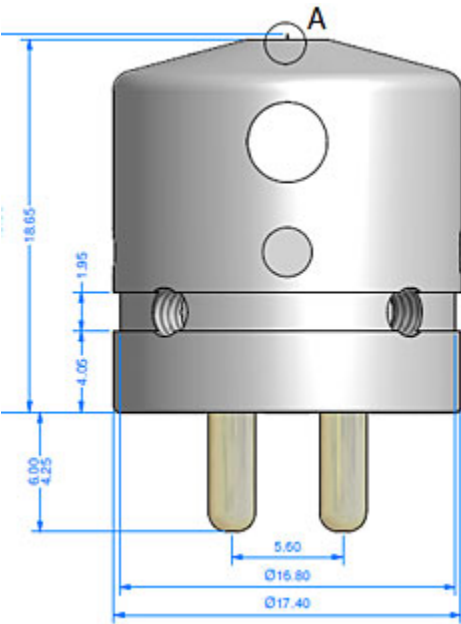
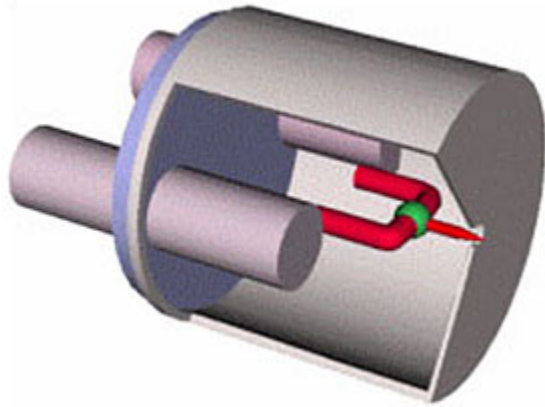
# The Schottky Emission Gun



The emitter is heated to 1800K causing ZrO to migrate from the bead to the emitter tip.

The ZrO is adsorbed onto the emitter tip which lowers the work function to 2.9eV

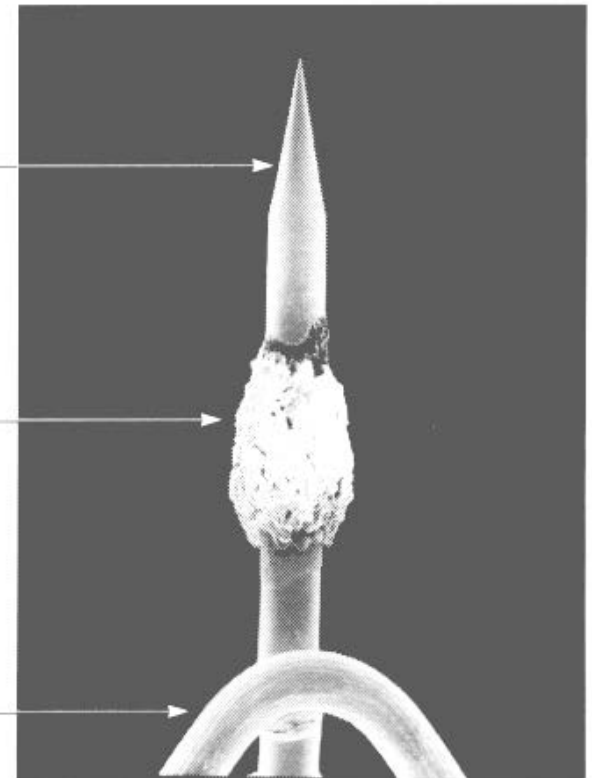
# Schottky Emitter Tip



<100> W Crystal

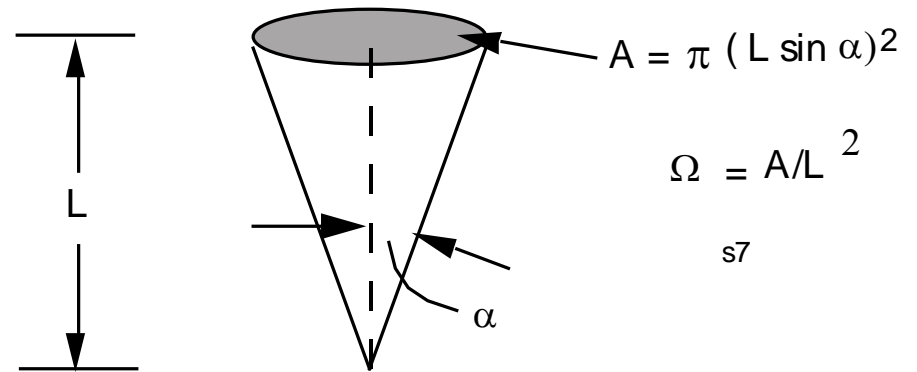
ZrO Reservoir

Polycrystalline tungsten heating filament

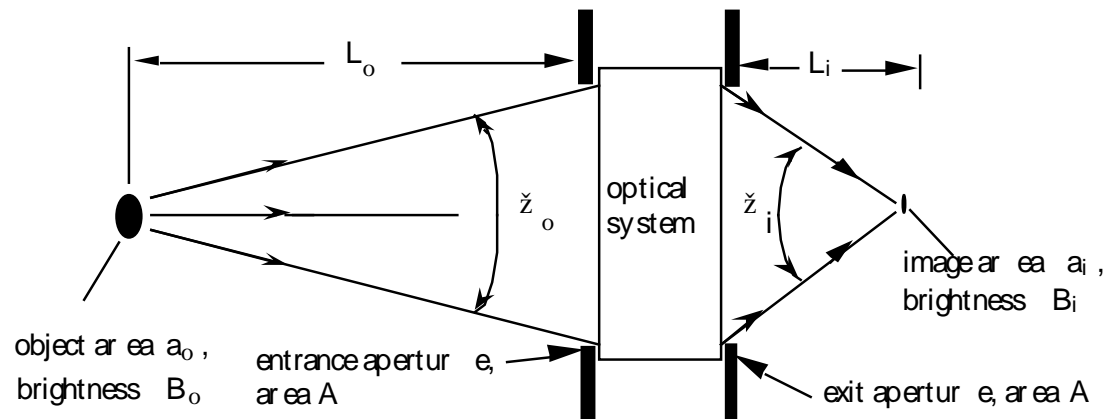


# Source Brightness

Units for Brightness:  
*amp / (cm<sup>2</sup> • steradian)*



Brightness is conserved



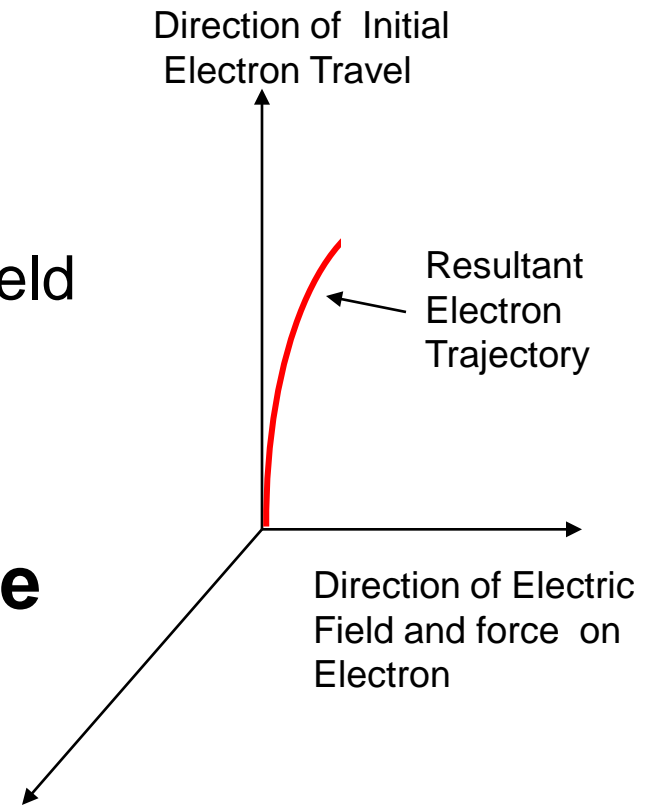
# Current Electron Sources

Source	Lifetime (hrs)	B @ 25 KV (amp/cm <sup>2</sup> Sr)	$\Delta E$ (eV)	Applications
W	100	$2 \times 10^5$ @ 2900 K	2-3	Low cost SEM
LaB <sub>6</sub>	1000	$5 \times 10^6$ @ 2000 K	2-3	SEM, shaped-beam lithography system
W, FE tip, "cold"	>1000	$5 \times 10^8 - 10^9$	0.5	High resolution SEM
Zr/O/W thermal FE	>1000	$2 \times 10^8$ @ 1800K	0.5	SEM and Gaussian-beam lithography

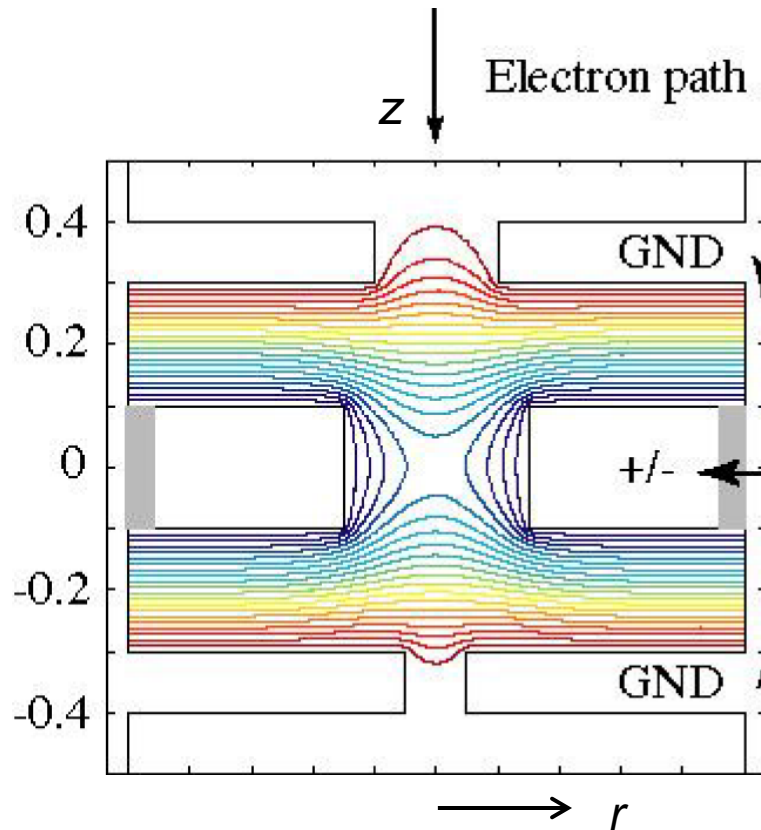


# Electrons in Electrostatic Fields

- **Electrons are accelerated towards any positive voltage.**
- **The acceleration force:**
  - Is proportional to the electric field strength (volts/distance).
  - Is in the same direction as the field.
- **The velocity and energy of the electron are increased.**
- **There is no rotation effect.**



# Electrostatic Lenses for charged particles



Axially symmetric  
potential distribution

3~5 orders more effective  
than magnetic lenses

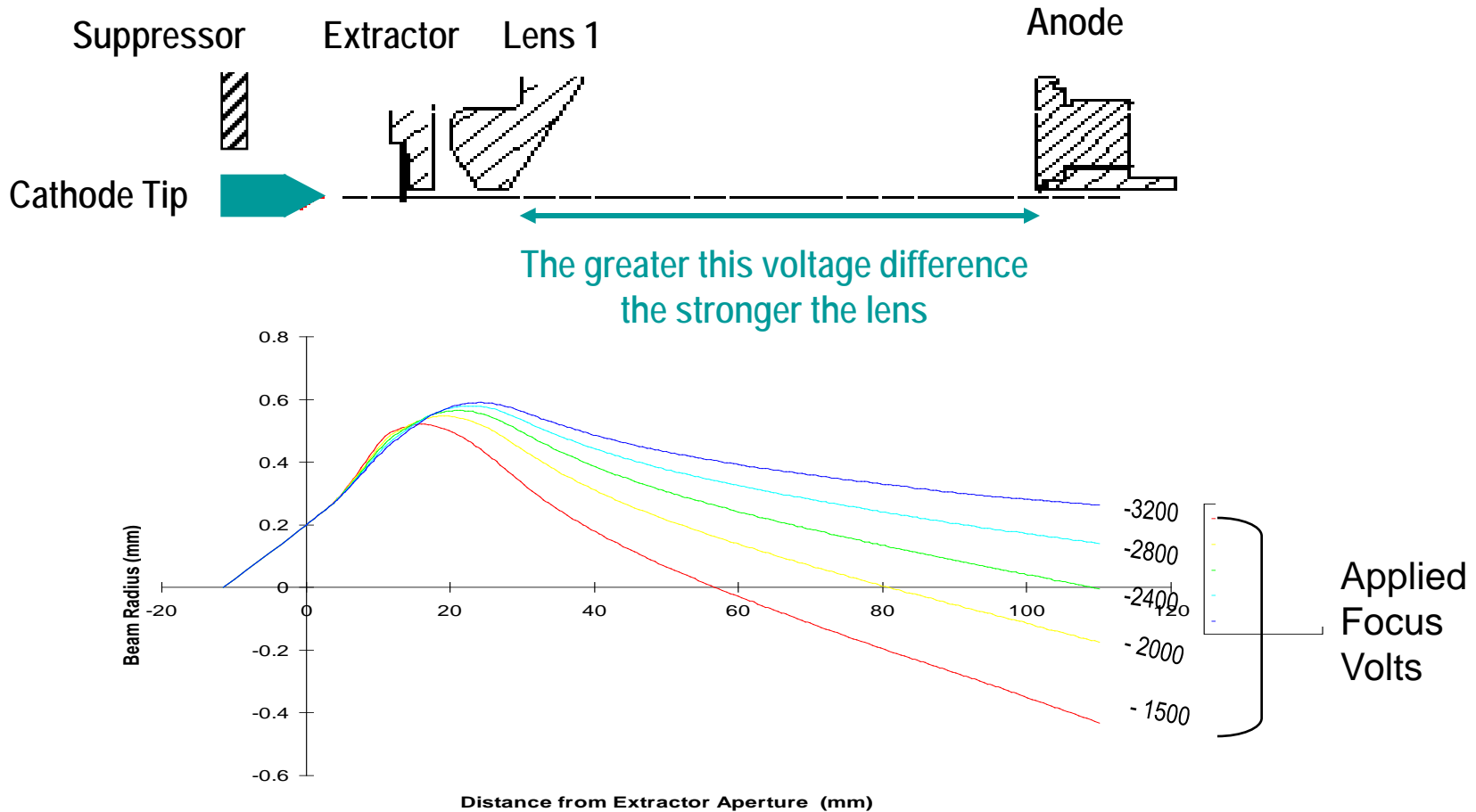
Electrodes of the Einzel lens

Subject to contamination  
build up → charging  
and distortion

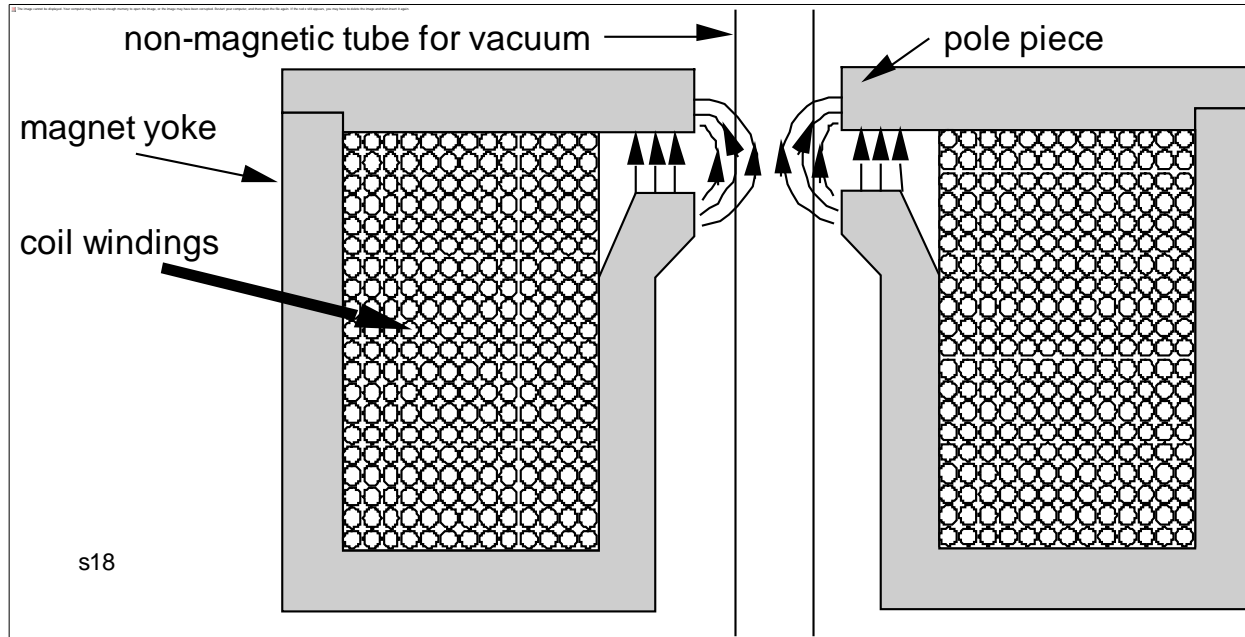
$$\Delta v_r = \int \frac{qE_r(r, z)}{mv_z} dz$$

$\Delta v_r$ : the change in radial velocity of a charge particle.

# Electron paths through the Electrostatic Lens



# Magnetic Lenses for charged particles



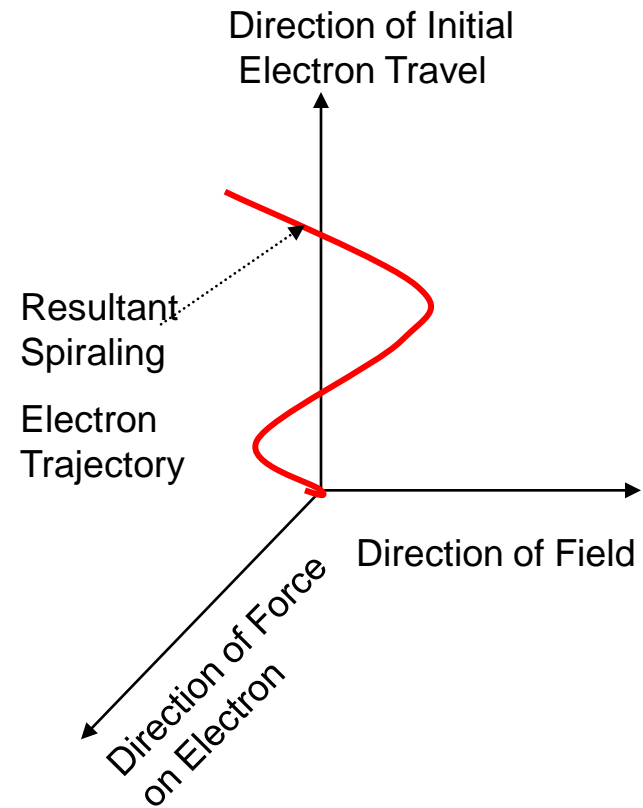
Axially symmetric field distribution

No contamination build up: can be outside vacuum.

Weak focusing, proportional to  $q/m$ , can not focus heavy ions in FIB

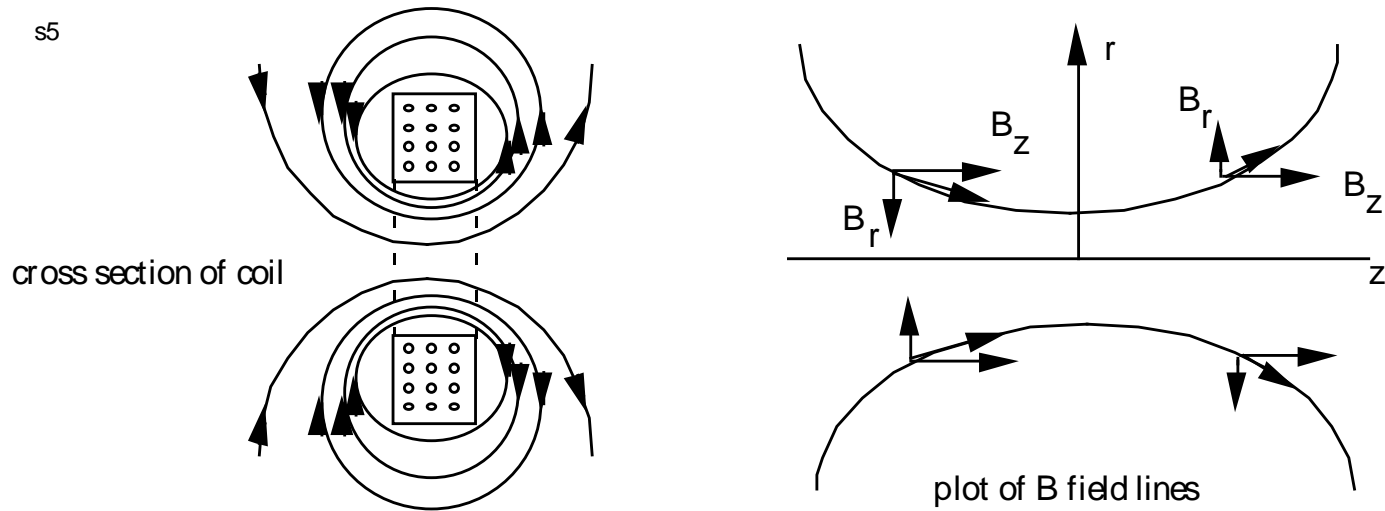
# Electrons in Magnetic Fields: The Left hand Rule

- An electron moving through a magnetic field receives an accelerating force which is:
  - perpendicular to the direction of the field
  - perpendicular to the direction of the electron
  - proportional to the flux density in the field
  - proportional to the speed of the electron
- **The velocity of the electron is not altered.**
- This means:
  - Electrons travelling parallel to the field are not affected.
  - In general, electrons travel through the field in some form of corkscrew path.



$$F \propto q (\vec{v} \times \vec{B})$$

# How do Magnetic Lenses work?



The axial and radial magnetic fields vary along the lens axis; roughly sketched as the following:

